Hideo Ohno

List of Publications by Year in Descending Order

732 papers	56,866 citations	90 h-index	228 g-index
781 ext. papers	61,621 ext. citations	4.5 avg, IF	7.84 L-index

#	Paper	IF	Citations
732	Nanometer-thin L10-MnAl film with B2-CoAl underlayer for high-speed and high-density STT-MRAM: Structure and magnetic properties. *Applied Physics Letters*, **2022**, 120, 052404	3.4	0
731	Generalized scaling of spin qubit coherence in over 12,000 host materials.. *Proceedings of the National Academy of Sciences of the United States of America*, **2022**, 119, e2121808119	11.5	7
730	Observation of domain structure in non-collinear antiferromagnetic Mn3Sn thin films by magneto-optical Kerr effect. *Applied Physics Letters*, **2022**, 120, 172405	3.4	3
729	Memristive control of mutual spin Hall nano-oscillator synchronization for neuromorphic computing. *Nature Materials*, **2021**,	27	12
728	Dilute Magnetic Materials **2021**, 923-978		
727	Theory of relaxation time of stochastic nanomagnets. *Physical Review B*, **2021**, 103,	3.3	6
726	Nanosecond Random Telegraph Noise in In-Plane Magnetic Tunnel Junctions. *Physical Review Letters*, **2021**, 126, 117202	7.4	20
725	Field-free and sub-ns magnetization switching of magnetic tunnel junctions by combining spin-transfer torque and spin□rbit torque. *Applied Physics Letters*, **2021**, 118, 092406	3.4	13
724	Double-Free-Layer Magnetic Tunnel Junctions for Probabilistic Bits. *Physical Review Applied*, **2021**, 15,	4.3	4
723	Chiral-spin rotation of non-collinear antiferromagnet by spin-orbit torque. *Nature Materials*, **2021**, 20, 1364-1370	27	16
722	Electrically connected spin-torque oscillators array for 2.4 GHz WiFi band transmission and energy harvesting. *Nature Communications*, **2021**, 12, 2924	17.4	13
721	Correlation of anomalous Hall effect with structural parameters and magnetic ordering in Mn3+xSn1□ thin films. *AIP Advances*, **2021**, 11, 065318	1.5	3
720	Unconventional Hall effect and its variation with Co-doping in van der Waals FeGeTe. *Scientific Reports*, **2021**, 11, 14121	4.9	1
719	Magnetization processes and magnetic domain structures in Ta/CoFeB/MgO stacks. *Journal of Magnetism and Magnetic Materials*, **2021**, 529, 167699	2.8	1
718	. *IEEE Journal of Solid-State Circuits*, **2021**, 56, 1116-1128	5.5	10
717	Temperature dependence of the energy barrier in X/1X nm shape-anisotropy magnetic tunnel junctions. *Applied Physics Letters*, **2021**, 118, 012409	3.4	5
716	Dilute Magnetic Materials **2021**, 1-56		

715	Coherent magnetization reversal of a cylindrical nanomagnet in shape-anisotropy magnetic tunnel junctions. *Applied Physics Letters*, **2021**, 118, 082404	3.4	0
714	Sigmoidal curves of stochastic magnetic tunnel junctions with perpendicular easy axis. *Applied Physics Letters*, **2021**, 119, 132406	3.4	3
713	Temperature dependence of intrinsic critical current in perpendicular easy axis CoFeB/MgO magnetic tunnel junctions. *Applied Physics Letters*, **2021**, 119, 242403	3.4	2
712	Complex switching behavior of magnetostatically coupled single-domain nanomagnets probed by micro-Hall magnetometry. *Applied Physics Letters*, **2020**, 116, 102401	3.4	2
711	Visualizing Magnetic Structure in 3D Nanoscale Ni-Fe Gyroid Networks. *Nano Letters*, **2020**, 20, 3642-3650	11.5	8
710	Neuromorphic computing with antiferromagnetic spintronics. *Journal of Applied Physics*, **2020**, 128, 010902	2.5	22
709	Composition dependence of spin□orbit torque in Pt1□xMnx/CoFeB heterostructures. *Applied Physics Letters*, **2020**, 117, 012402	3.4	5
708	Current distribution in metallic multilayers from resistance measurements. *Physical Review B*, **2020**, 101,	3.3	2
707	**2020**,		9
706	Crystal orientation and anomalous Hall effect of sputter-deposited non-collinear antiferromagnetic Mn3Sn thin films. *Applied Physics Express*, **2020**, 13, 013001	2.4	13
705	Energy Efficient Control of Ultrafast Spin Current to Induce Single Femtosecond Pulse Switching of a Ferromagnet. *Advanced Science*, **2020**, 7, 2001996	13.6	6
704	Multidomain Memristive Switching of Pt38Mn62/[Co/Ni]n Multilayers. *Physical Review Applied*, **2020**, 14,	4.3	5
703	Probing edge condition of nanoscale CoFeB/MgO magnetic tunnel junctions by spin-wave resonance. *Applied Physics Letters*, **2020**, 117, 202404	3.4	1
702	Engineering Single-Shot All-Optical Switching of Ferromagnetic Materials. *Nano Letters*, **2020**, 20, 8654-8660	11.5	9
701	Spin-orbit torque switching of an antiferromagnetic metallic heterostructure. *Nature Communications*, **2020**, 11, 5715	17.4	12
700	Giant voltage-controlled modulation of spin Hall nano-oscillator damping. *Nature Communications*, **2020**, 11, 4006	17.4	18
699	Dual-Port Field-Free SOT-MRAM Achieving 90-MHz Read and 60-MHz Write Operations under 55-nm CMOS Technology and 1.2-V Supply Voltage **2020**,		9
698	Scaling magnetic tunnel junction down to single-digit nanometers□challenges and prospects. *Applied Physics Letters*, **2020**, 116, 160501	3.4	27

697	Spin-transfer-torque magnetoresistive random-access memory (STT-MRAM) technology **2019**, 237-281		7
696	Neuromorphic Computing: Artificial Neuron and Synapse Realized in an Antiferromagnet/Ferromagnet Heterostructure Using Dynamics of Spin□Orbit Torque Switching (Adv. Mater. 23/2019). *Advanced Materials*, **2019**, 31, 1970167	24	1
695	Artificial Neuron and Synapse Realized in an Antiferromagnet/Ferromagnet Heterostructure Using Dynamics of Spin-Orbit Torque Switching. *Advanced Materials*, **2019**, 31, e1900636	24	75
694	Reversal of domain wall chirality with ferromagnet thickness in W/(Co)FeB/MgO systems. *Applied Physics Letters*, **2019**, 114, 042405	3.4	2
693	Spin-Pumping-Free Determination of Spin-Orbit Torque Efficiency from Spin-Torque Ferromagnetic Resonance. *Physical Review Applied*, **2019**, 12,	4.3	12
692	A 47.14- $mutext{W}$ 200-MHz MOS/MTJ-Hybrid Nonvolatile Microcontroller Unit Embedding STT-MRAM and FPGA for IoT Applications. *IEEE Journal of Solid-State Circuits*, **2019**, 54, 2991-3004	5.5	22
691	Families of magnetic semiconductors □an overview. *Journal of Semiconductors*, **2019**, 40, 080301	2.3	22
690	Properties of sputtered full Heusler alloy Cr2MnSb and its application in a magnetic tunnel junction. *Journal Physics D: Applied Physics*, **2019**, 52, 495002	3	4
689	Magnetization dynamics and related phenomena in semiconductors with ferromagnetism. *Journal of Semiconductors*, **2019**, 40, 081502	2.3	
688	Write-error rate of nanoscale magnetic tunnel junctions in the precessional regime. *Applied Physics Letters*, **2019**, 115, 142406	3.4	4
687	Formation and current-induced motion of synthetic antiferromagnetic skyrmion bubbles. *Nature Communications*, **2019**, 10, 5153	17.4	73
686	Giant perpendicular magnetic anisotropy in Ir/Co/Pt multilayers. *Physical Review Materials*, **2019**, 3,	3.2	17
685	Electric-Field Controlled Magnetism **2019**, 519-541		
684	**2019**,		19
683	Stack structure and temperature dependence of spin-orbit torques in heterostructures with antiferromagnetic PtMn. *Applied Physics Letters*, **2019**, 115, 242404	3.4	3
682	Integer factorization using stochastic magnetic tunnel junctions. *Nature*, **2019**, 573, 390-393	50.4	140
681	Spin-orbit torque-induced switching of in-plane magnetized elliptic nanodot arrays with various easy-axis directions measured by differential planar Hall resistance. *Applied Physics Letters*, **2019**, 114, 012410	3.4	13
680	Spin transport and spin torque in antiferromagnetic devices. *Nature Physics*, **2018**, 14, 220-228	16.2	178

679	Shape anisotropy revisited in single-digit nanometer magnetic tunnel junctions. *Nature Communications*, **2018**, 9, 663	17.4	96
678	Time and spatial evolution of spin□rbit torque-induced magnetization switching in W/CoFeB/MgO structures with various sizes. *Japanese Journal of Applied Physics*, **2018**, 57, 04FN02	1.4	8
677	Electric-field effect on magnetic anisotropy in Pt/Co/Pd/MgO structures deposited on GaAs and Si substrates. *Applied Physics Express*, **2018**, 11, 013003	2.4	11
676	Temperature dependence of ferromagnetic resonance spectra of permalloy on (Bi1□x Sb x)2Te3. *Japanese Journal of Applied Physics*, **2018**, 57, 020302	1.4	3
675	Electric-field effect on the easy cone angle of the easy-cone state in CoFeB/MgO investigated by ferromagnetic resonance. *Applied Physics Letters*, **2018**, 112, 172402	3.4	8
674	Free-layer size dependence of anisotropy field in nanoscale CoFeB/MgO magnetic tunnel junctions. *Applied Physics Express*, **2018**, 11, 043001	2.4	4
673	Fabrication and characterization of sub-micron scale hall devices from 2-dimensional electron gas at the heterostrutcure of GaAs/AlGaAs **2018**,		1
672	Evidence for Ferromagnetic Clusters in the Colossal-Magnetoresistance Material EuB_{6}. *Physical Review Letters*, **2018**, 120, 257201	7.4	18
671	Scalability and wide temperature range operation of spin-orbit torque switching devices using Co/Pt multilayer nanowires. *Applied Physics Letters*, **2018**, 113, 212403	3.4	7
670	Angle dependent magnetoresistance in heterostructures with antiferromagnetic and non-magnetic metals. *Applied Physics Letters*, **2018**, 113, 202404	3.4	8
669	Evaluation of energy barrier of CoFeB/MgO magnetic tunnel junctions with perpendicular easy axis using retention time measurement. *Japanese Journal of Applied Physics*, **2018**, 57, 04FN08	1.4	16
668	Temperature-dependent properties of CoFeB/MgO thin films: Experiments versus simulations. *Physical Review B*, **2018**, 98,	3.3	29
667	An effect of capping-layer material on interfacial anisotropy and thermal stability factor of MgO/CoFeB/Ta/CoFeB/MgO/capping-layer structure. *Applied Physics Letters*, **2018**, 113, 172401	3.4	4
666	Perspective: Spintronic synapse for artificial neural network. *Journal of Applied Physics*, **2018**, 124, 151904	2.5	45
665	Preface to Special Topic: New Physics and Materials for Neuromorphic Computation. *Journal of Applied Physics*, **2018**, 124, 151801	2.5	7
664	Characterization of spin□rbit torque-controlled synapse device for artificial neural network applications. *Japanese Journal of Applied Physics*, **2018**, 57, 1002B2	1.4	12
663	Non-linear variation of domain period under electric field in demagnetized CoFeB/MgO stacks with perpendicular easy axis. *Applied Physics Letters*, **2018**, 112, 202402	3.4	4
662	Spin-orbit torques in high-resistivity-W/CoFeB/MgO. *Applied Physics Letters*, **2018**, 112, 192408	3.4	52

661	Origin of variation of shift field via annealing at 400°C in a perpendicular-anisotropy magnetic tunnel junction with [Co/Pt]-multilayers based synthetic ferrimagnetic reference layer. *AIP Advances*, **2017**, 7, 055913	1.5	6
660	Damping constant in a free layer in nanoscale CoFeB/MgO magnetic tunnel junctions investigated by homodyne-detected ferromagnetic resonance. *Applied Physics Express*, **2017**, 10, 013001	2.4	7
659	Magnetic domain-wall creep driven by field and current in Ta/CoFeB/MgO. *AIP Advances*, **2017**, 7, 055918	1.5	5
658	Ferromagnetic resonance spectra of Py deposited on (Bi1-xSbx)2Te3. *AIP Advances*, **2017**, 7, 055919	1.5	5
657	Device-size dependence of field-free spin-orbit torque induced magnetization switching in antiferromagnet/ferromagnet structures. *Applied Physics Letters*, **2017**, 110, 092410	3.4	50
656	Atomic structure and electronic properties of MgO grain boundaries in tunnelling magnetoresistive devices. *Scientific Reports*, **2017**, 7, 45594	4.9	26
655	Impact of Tungsten Sputtering Condition on Magnetic and Transport Properties of Double-MgO Magnetic Tunneling Junction With CoFeB/W/CoFeB Free Layer. *IEEE Transactions on Magnetics*, **2017**, 53, 1-4	2	16
654	Stack Structure Dependence of Magnetic Properties of PtMn/[Co/Ni] Films for Spin-Orbit Torque Switching Device. *IEEE Transactions on Magnetics*, **2017**, 53, 1-4	2	11
653	Electric-field-induced magnetization switching in CoFeB/MgO magnetic tunnel junctions. *Japanese Journal of Applied Physics*, **2017**, 56, 0802A3	1.4	1
652	Annealing temperature dependence of magnetic properties of CoFeB/MgO stacks on different buffer layers. *Japanese Journal of Applied Physics*, **2017**, 56, 0802B2	1.4	11
651	Magnetization switching schemes for nanoscale three-terminal spintronics devices. *Japanese Journal of Applied Physics*, **2017**, 56, 0802A1	1.4	36
650	Design of a variation-resilient single-ended non-volatile six-input lookup table circuit with a redundant-magnetic tunnel junction-based active load for smart Internet-of-things applications. *Electronics Letters*, **2017**, 53, 456-458	1.1	5
649	Magnetization dynamics and its scattering mechanism in thin CoFeB films with interfacial anisotropy. *Proceedings of the National Academy of Sciences of the United States of America*, **2017**, 114, 3815-3820	11.5	35
648	Analogue spin-orbit torque device for artificial-neural-network-based associative memory operation. *Applied Physics Express*, **2017**, 10, 013007	2.4	107
647	A spin transfer torque magnetoresistance random access memory-based high-density and ultralow-power associative memory for fully data-adaptive nearest neighbor search with current-mode similarity evaluation and time-domain minimum searching. *Japanese Journal of Applied Physics*, **2017**, 56, 04CF08	1.4	2
646	Magnetic-field-angle dependence of coercivity in CoFeB/MgO magnetic tunnel junctions with perpendicular easy axis. *Applied Physics Letters*, **2017**, 111, 132407	3.4	16
645	Magnetic and Free-Layer Properties of MgO/(Co)FeB/MgO Structures: Dependence on CoFeB Composition. *IEEE Magnetics Letters*, **2017**, 8, 1-3	1.6	12
644	Electric-field effect on spin-wave resonance in a nanoscale CoFeB/MgO magnetic tunnel junction. *Applied Physics Letters*, **2017**, 111, 072403	3.4	14

643	Spintronics based random access memory: a review. *Materials Today*, **2017**, 20, 530-548	21.8	401
642	Spin-orbit torque induced magnetization switching in Co/Pt multilayers. *Applied Physics Letters*, **2017**, 111, 102402	3.4	20
641	Magnetic and transport properties of Sb2Te3 doped with high concentration of Cr. *Applied Physics Express*, **2017**, 10, 103001	2.4	11
640	Magnetic tunnel junctions with perpendicular easy axis at junction diameter of less than 20 nm. *Japanese Journal of Applied Physics*, **2017**, 56, 0802A6	1.4	14
639	Magnetic properties of FeV/MgO-based structures. *Applied Physics Express*, **2017**, 10, 083001	2.4	3
638	Spin-orbit torques and Dzyaloshinskii-Moriya interaction in PtMn/[Co/Ni] heterostructures. *Applied Physics Letters*, **2017**, 111, 182412	3.4	12
637	Fast neutron tolerance of the perpendicular-anisotropy CoFeB MgO magnetic tunnel junctions with junction diameters between 46 and 64 nm. *Japanese Journal of Applied Physics*, **2017**, 56, 0802B3	1.4	3
636	Current-induced magnetization switching in a nano-scale CoFeB-MgO magnetic tunnel junction under in-plane magnetic field. *AIP Advances*, **2017**, 7, 055927	1.5	5
635	Fabrication of a magnetic-tunnel-junction-based nonvolatile logic-in-memory LSI with content-aware write error masking scheme achieving 92% storage capacity and 79% power reduction. *Japanese Journal of Applied Physics*, **2017**, 56, 04CN01	1.4	7
634	Soft errors in 10-nm-scale magnetic tunnel junctions exposed to high-energy heavy-ion radiation. *Japanese Journal of Applied Physics*, **2017**, 56, 0802B4	1.4	12
633	Use of analog spintronics device in performing neuro-morphic computing functions **2017**,		1
632	Magnetic stray-field studies of a single Cobalt nanoelement as a component of the building blocks of artificial square spin ice. *Journal of Magnetism and Magnetic Materials*, **2016**, 400, 206-212	2.8	12
631	. *Proceedings of the IEEE*, **2016**, 104, 1844-1863	14.3	70
630	Fermi level position, Coulomb gap, and Dresselhaus splitting in (Ga,Mn)As. *Scientific Reports*, **2016**, 6, 27266	4.9	18
629	Study on initial current leakage spots in CoFeB-capped MgO tunnel barrier by conductive atomic force microscopy. *Japanese Journal of Applied Physics*, **2016**, 55, 04EE05	1.4	3
628	Temperature dependence of in-plane magnetic anisotropy and anisotropic magnetoresistance in (Ga,Mn)As codoped with Li. *Applied Physics Letters*, **2016**, 108, 112404	3.4	5
627	A 600- W ultra-low-power associative processor for image pattern recognition employing magnetic tunnel junction-based nonvolatile memories with autonomic intelligent power-gating scheme. *Japanese Journal of Applied Physics*, **2016**, 55, 04EF15	1.4	9
626	Demonstration of Yield Improvement for On-Via MTJ Using a 2-Mbit 1T-1MTJ STT-MRAM Test Chip **2016**,		5

625	. *IEEE Transactions on Magnetics*, **2016**, 52, 1-4	2	13
624	Adiabatic spin-transfer-torque-induced domain wall creep in a magnetic metal. *Nature Physics*, **2016**, 12, 333-336	16.2	32
623	A spin-orbit torque switching scheme with collinear magnetic easy axis and current configuration. *Nature Nanotechnology*, **2016**, 11, 621-5	28.7	311
622	Magnetization switching by spin-orbit torque in an antiferromagnet-ferromagnet bilayer system. *Nature Materials*, **2016**, 15, 535-41	27	534
621	Atomic-Scale Structure and Local Chemistry of CoFeB-MgO Magnetic Tunnel Junctions. *Nano Letters*, **2016**, 16, 1530-6	11.5	69
620	Improvement of Thermal Tolerance of CoFeB□MgO Perpendicular-Anisotropy Magnetic Tunnel Junctions by Controlling Boron Composition. *IEEE Transactions on Magnetics*, **2016**, 52, 1-4	2	14
619	Current-Induced Magnetization Switching of CoFeB/Ta/[Co/Pd (Pt)]-Multilayers in Magnetic Tunnel Junctions With Perpendicular Anisotropy. *IEEE Transactions on Magnetics*, **2016**, 52, 1-4	2	5
618	Magnetization Reversal by Field and Current Pulses in Elliptic CoFeB/MgO Tunnel Junctions With Perpendicular Easy Axis. *IEEE Magnetics Letters*, **2016**, 7, 1-4	1.6	11
617	Beyond MRAM: Nonvolatile Logic-in-Memory VLSI **2016**, 199-230		1
616	Critical role of W deposition condition on spin-orbit torque induced magnetization switching in nanoscale W/CoFeB/MgO. *Applied Physics Letters*, **2016**, 109, 192405	3.4	53
615	Stochastic behavior-considered VLSI CAD environment for MTJ/MOS-hybrid microprocessor design **2016**,		3
614	Electric field control of Skyrmions in magnetic nanodisks. *Applied Physics Letters*, **2016**, 108, 152403	3.4	43
613	Peculiar temperature dependence of electric-field effect on magnetic anisotropy in Co/Pd/MgO system. *Applied Physics Letters*, **2016**, 109, 082403	3.4	33
612	Effect of electric-field modulation of magnetic parameters on domain structure in MgO/CoFeB. *AIP Advances*, **2016**, 6, 075017	1.5	24
611	Electric-field-induced magnetization switching in CoFeB/MgO magnetic tunnel junctions with high junction resistance. *Applied Physics Letters*, **2016**, 108, 192406	3.4	58
610	An Overview of Nonvolatile Emerging Memories□Spintronics for Working Memories. *IEEE Journal on Emerging and Selected Topics in Circuits and Systems*, **2016**, 6, 109-119	5.2	88
609	Current-induced domain wall motion in magnetic nanowires with various widths down to less than 20 nm. *Japanese Journal of Applied Physics*, **2016**, 55, 04EN01	1.4	5
608	A sub-ns three-terminal spin-orbit torque induced switching device **2016**,		20

607	Free- and reference-layer magnetization modes versus in-plane magnetic field in a magnetic tunnel junction with perpendicular magnetic easy axis. *Physical Review B*, **2016**, 94,	3.3	4
606	Spintronics. *Proceedings of the IEEE*, **2016**, 104, 1782-1786	14.3	15
605	In-plane anisotropy of a nano-scaled magnetic tunnel junction with perpendicular magnetic easy axis. *Japanese Journal of Applied Physics*, **2015**, 54, 04DM03	1.4	4
604	Ferromagnetic resonance in nanoscale CoFeB/MgO magnetic tunnel junctions. *Journal of Applied Physics*, **2015**, 117, 17B708	2.5	13
603	Evidence of a reduction reaction of oxidized iron/cobalt by boron atoms diffused toward naturally oxidized surface of CoFeB layer during annealing. *Applied Physics Letters*, **2015**, 106, 142407	3.4	9
602	Nanocluster building blocks of artificial square spin ice: Stray-field studies of thermal dynamics. *Journal of Applied Physics*, **2015**, 117, 17C746	2.5	13
601	Inverse spin Hall effect in Pt/(Ga,Mn)As. *Applied Physics Letters*, **2015**, 106, 222405	3.4	4
600	**2015**,		1
599	Spin-orbit torque induced magnetization switching in nano-scale Ta/CoFeB/MgO. *Applied Physics Letters*, **2015**, 107, 012401	3.4	131
598	Fabrication of a 3000-6-input-LUTs embedded and block-level power-gated nonvolatile FPGA chip using p-MTJ-based logic-in-memory structure **2015**,		2
597	Ferromagnetic resonance of Py deposited on ZnO grown by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2015**, 54, 093001	1.4	3
596	Challenge of MTJ-based nonvolatile logic-in-memory architecture for ultra low-power and highly dependable VLSI computing **2015**,		1
595	Nonvolatile Logic-in-Memory LSI Using Cycle-Based Power Gating and its Application to Motion-Vector Prediction. *IEEE Journal of Solid-State Circuits*, **2015**, 50, 476-489	5.5	43
594	Magnetic Semiconductors **2015**, 649-682		
593	Proposal and demonstration of a new spin-orbit torque induced switching device **2015**,		2
592	Electric-Field Modulation of Damping Constant in a Ferromagnetic Semiconductor (Ga,Mn)As. *Physical Review Letters*, **2015**, 115, 057204	7.4	19
591	Dependence of magnetic properties of MgO/CoFeB/Ta stacks on CoFeB and Ta thicknesses. *Japanese Journal of Applied Physics*, **2015**, 54, 04DM04	1.4	6
590	Vertical electric field induced suppression of fine structure splitting of excited state excitons in a single GaAs/AlGaAs island quantum dots. *Applied Physics Letters*, **2015**, 107, 123102	3.4	2

589	Electric-field induced nonlinear ferromagnetic resonance in a CoFeB/MgO magnetic tunnel junction. *Applied Physics Letters*, **2015**, 107, 132404	3.4	12
588	Temperature dependence of energy barrier in CoFeB-MgO magnetic tunnel junctions with perpendicular easy axis. *Applied Physics Letters*, **2015**, 107, 152405	3.4	20
587	Noise spectroscopy studies of GaAs/AlGaAs hall devices for optimizing micro- and nano-scale magnetic measurements **2015**,		1
586	Properties of perpendicular-anisotropy magnetic tunnel junctions fabricated over the bottom electrode contact. *Japanese Journal of Applied Physics*, **2015**, 54, 04DM06	1.4	4
585	Power-gated 32 bit microprocessor with a power controller circuit activated by deep-sleep-mode instruction achieving ultra-low power operation. *Japanese Journal of Applied Physics*, **2015**, 54, 04DE08	1.4	7
584	Thermal stability of a magnetic domain wall in nanowires. *Physical Review B*, **2015**, 91,	3.3	18
583	Control of magnetism by electric fields. *Nature Nanotechnology*, **2015**, 10, 209-20	28.7	571
582	1T1MTJ STT-MRAM Cell Array Design with an Adaptive Reference Voltage Generator for Improving Device Variation Tolerance **2015**,		10
581	10 nmphi perpendicular-anisotropy CoFeB-MgO magnetic tunnel junction with over 400□C high thermal tolerance by boron diffusion control **2015**,		14
580	Driving Force in Diffusion and Redistribution of Reducing Agents During Redox Reaction on the Surface of CoFeB Film. *IEEE Transactions on Magnetics*, **2015**, 51, 1-4	2	1
579	CoFeB Thickness Dependence of Damping Constants for Single and Double CoFeB-MgO Interface Structures. *IEEE Magnetics Letters*, **2015**, 6, 1-3	1.6	27
578	Temperature dependence of lattice parameter of (Ga,Mn)As on GaAs substrate. *Japanese Journal of Applied Physics*, **2015**, 54, 098003	1.4	2
577	Localized precessional mode of domain wall controlled by magnetic field and dc current. *Applied Physics Express*, **2015**, 8, 023003	2.4	4
576	Magnetization reversal induced by in-plane current in Ta/CoFeB/MgO structures with perpendicular magnetic easy axis. *Journal of Applied Physics*, **2014**, 115, 17C714	2.5	28
575	Dilute ferromagnetic semiconductors: Physics and spintronic structures. *Reviews of Modern Physics*, **2014**, 86, 187-251	40.5	588
574	III□V-Based Ferromagnetic Semiconductors **2014**, 315-358		
573	Design and fabrication of a perpendicular magnetic tunnel junction based nonvolatile programmable switch achieving 40% less area using shared-control transistor structure. *Journal of Applied Physics*, **2014**, 115, 17B742	2.5	8
572	Analysis of single-event upset of magnetic tunnel junction used in spintronic circuits caused by radiation-induced current. *Journal of Applied Physics*, **2014**, 115, 17B748	2.5	4

571	A Nonvolatile Associative Memory-Based Context-Driven Search Engine Using 90 nm CMOS/MTJ-Hybrid Logic-in-Memory Architecture. *IEEE Journal on Emerging and Selected Topics in Circuits and Systems*, **2014**, 4, 460-474	5.2	21
570	Electric-field effects on magnetic anisotropy and damping constant in Ta/CoFeB/MgO investigated by ferromagnetic resonance. *Applied Physics Letters*, **2014**, 105, 052415	3.4	89
569	10.5 A 90nm 20MHz fully nonvolatile microcontroller for standby-power-critical applications **2014**,		52
568	Quantitative characterization of the spin-orbit torque using harmonic Hall voltage measurements. *Physical Review B*, **2014**, 89,	3.3	274
567	Interface control of the magnetic chirality in CoFeB/MgO heterostructures with heavy-metal underlayers. *Nature Communications*, **2014**, 5, 4655	17.4	260
566	DC voltages in Py and Py/Pt under ferromagnetic resonance. *Applied Physics Express*, **2014**, 7, 013002	2.4	29
565	Influence of Heavy Ion Irradiation on Perpendicular-Anisotropy CoFeB-MgO Magnetic Tunnel Junctions. *IEEE Transactions on Nuclear Science*, **2014**, 61, 1710-1716	1.7	26
564	Magnetization switching in a CoFeB/MgO magnetic tunnel junction by combining spin-transfer torque and electric field-effect. *Applied Physics Letters*, **2014**, 104, 212406	3.4	72
563	Spin-transfer-torque magnetoresistive random access memory (STT-MRAM) technology **2014**, 455-494		4
562	Advances in spintronics devices for microelectronics □From spin-transfer torque to spin-orbit torque **2014**,		5
561	Electric Field-Induced Magnetization Switching in CoFeB-MgO□tatic Magnetic Field Angle Dependence. *IEEE Transactions on Magnetics*, **2014**, 50, 1-3	2	2
560	Anomalous temperature dependence of current-induced torques in CoFeB/MgO heterostructures with Ta-based underlayers. *Physical Review B*, **2014**, 89,	3.3	80
559	Effect of spin Hall torque on current-induced precessional domain wall motion. *Applied Physics Express*, **2014**, 7, 033005	2.4	14
558	Electric-field effects on magnetic properties of molecular beam epitaxially grown thin (Ga,Mn)Sb layers. *Journal of Crystal Growth*, **2014**, 401, 633-635	1.6	3
557	Trend of tunnel magnetoresistance and variation in threshold voltage for keeping data load robustness of metal□xide□emiconductor/magnetic tunnel junction hybrid latches. *Journal of Applied Physics*, **2014**, 115, 17C728	2.5	8
556	Three-terminal magnetic tunneling junction device with perpendicular anisotropy CoFeB sensing layer. *Journal of Applied Physics*, **2014**, 115, 17B750	2.5	6
555	Co/Pt multilayer-based magnetic tunnel junctions with a CoFeB/Ta insertion layer. *Journal of Applied Physics*, **2014**, 115, 17C719	2.5	20
554	Design of an energy-efficient 2T-2MTJ nonvolatile TCAM based on a parallel-serial-combined search scheme. *IEICE Electronics Express*, **2014**, 11, 20131006-20131006	0.5	9

553	Complementary 5T-4MTJ nonvolatile TCAM cell circuit with phase-selective parallel writing scheme. *IEICE Electronics Express*, **2014**, 11, 20140297-20140297	0.5	6
552	A compact low-power nonvolatile flip-flop using domain-wall-motion-device-based single-ended structure. *IEICE Electronics Express*, **2014**, 11, 20140296-20140296	0.5	6
551	Process-induced damage and its recovery for a CoFeB□MgO magnetic tunnel junction with perpendicular magnetic easy axis. *Japanese Journal of Applied Physics*, **2014**, 53, 103001	1.4	15
550	Distribution of critical current density for magnetic domain wall motion. *Journal of Applied Physics*, **2014**, 115, 17D508	2.5	3
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